
2SB562

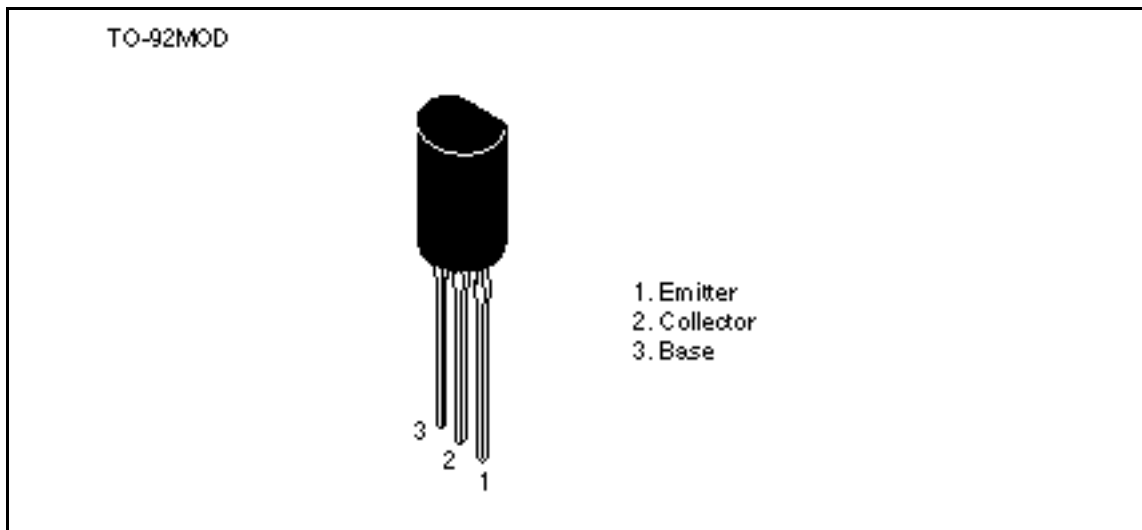
Silicon PNP Epitaxial

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Application

- Low frequency power amplifier
- Complementary pair with 2SD468

Outline



2SB562

Absolute Maximum Ratings (Ta = 25°C)

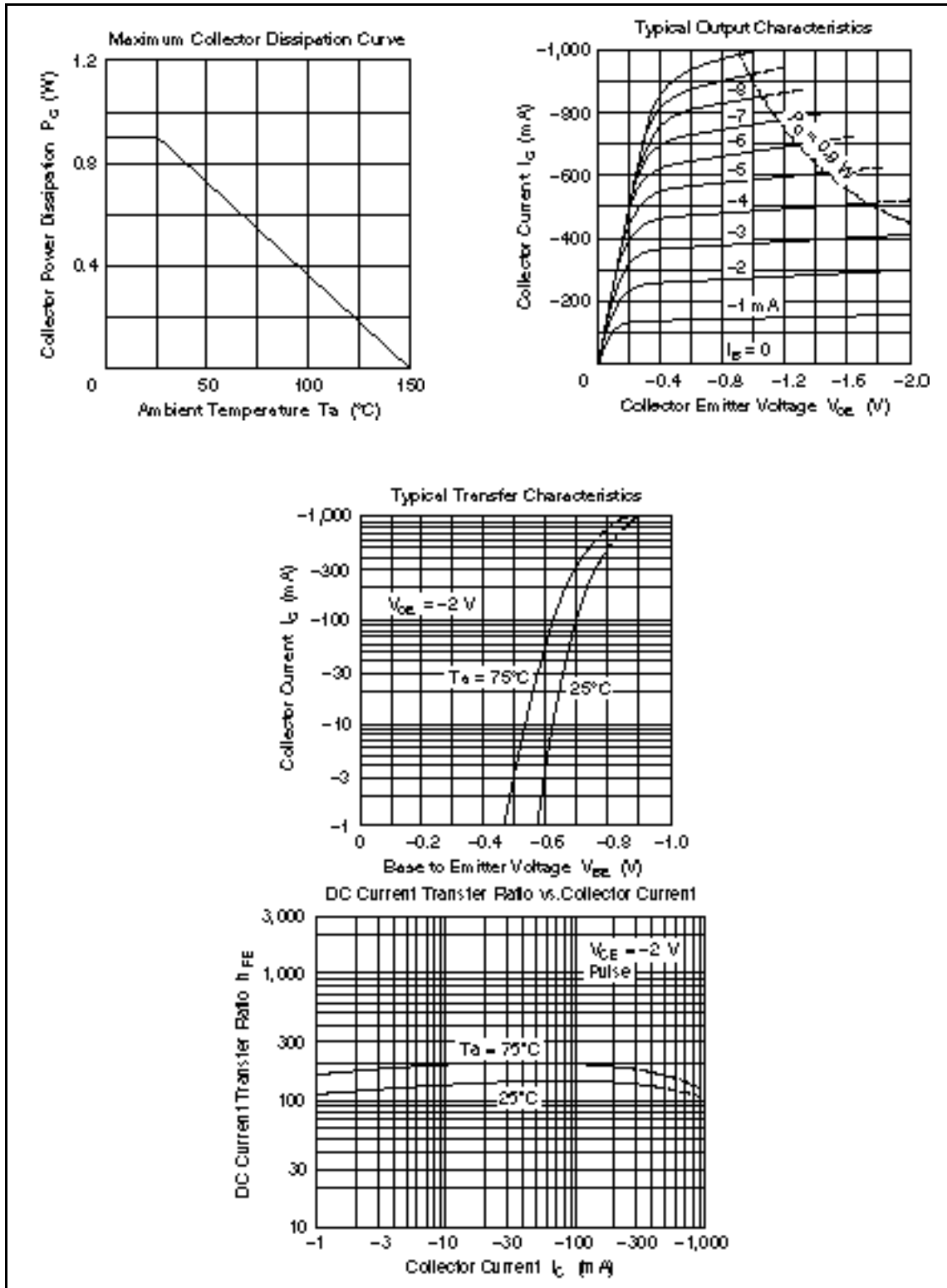
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-25	V
Collector to emitter voltage	V_{CEO}	-20	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-1.0	A
Collector peak current	$i_{C(\text{peak})}$	-1.5	A
Collector power dissipation	P_C	0.9	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

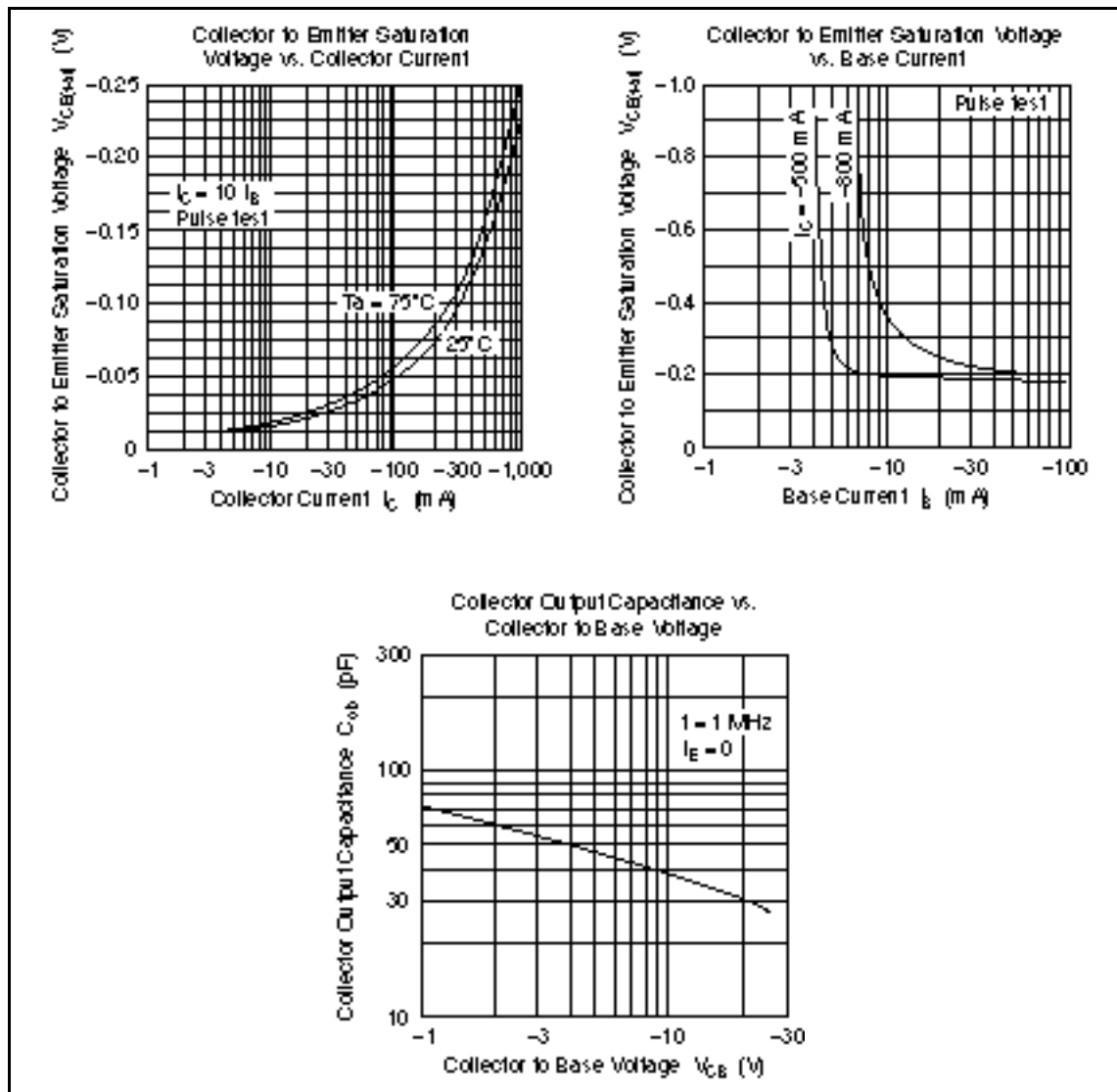
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-25	—	—	V	$I_C = -10 \mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-20	—	—	V	$I_C = -1 \text{ mA}$, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -10 \mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1.0	μA	$V_{CB} = -20 \text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE}^{*1}	85	—	240		$V_{CE} = -2 \text{ V}$, $I_C = -0.5 \text{ A}$ (Pulse test)
Collector to emitter saturation voltage	$V_{CE(\text{sat})}$	—	-0.2	-0.5	V	$I_C = -0.8 \text{ A}$, $I_B = -0.08 \text{ A}$ (Pulse test)
Base to emitter voltage	V_{BE}	—	-0.8	-1.0	V	$V_{CE} = -2 \text{ V}$, $I_C = -0.5 \text{ A}$ (Pulse test)
Gain bandwidth product	f_T	—	350	—	MHz	$V_{CE} = -2 \text{ V}$, $I_C = -0.5 \text{ A}$ (Pulse test)
Collector output capacitance	C_{ob}	—	38	—	pF	$V_{CB} = -10 \text{ V}$, $I_E = 0$ $f = 1 \text{ MHz}$

Note: 1. The 2SB562 is grouped by h_{FE} as follows.

B	C
85 to 170	120 to 240



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